优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
-60V	105mΩ @ V_{GS} = -10V	-7.3A
	130mΩ @ V_{GS} = -4.5V	-6.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

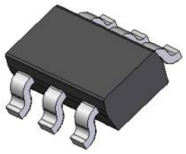
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed

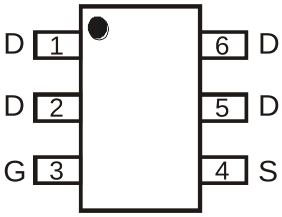
Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (Approximate)

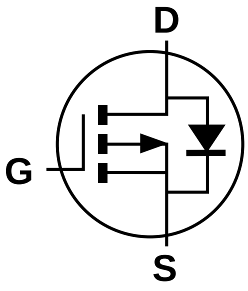
TSOT26



Top View



Device Schematic



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	T_C = +25°C	I_D	-7.3	A
	T_C = +70°C		-5.8	
Maximum Body Diode Forward Current (Note 6)		I_S	-1.8	A
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)		I_{DM}	-24	A
Avalanche Current (Note 7) L = 0.1mH		I_{AS}	-19	A
Repetitive Avalanche Energy (Note 7) L = 0.1mH		E_{AS}	18	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.2	W
	T_A = +70°C		0.75	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	105	°C/W
	t<10s		60	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.8	W
	T_A = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	69	°C/W
	t<10s		39	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	15	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -48V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	100	nA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	105	mΩ	V_{GS} = -10V, I_D = -4.5A
		—	—	130		V_{GS} = -4.5V, I_D = -3.5A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	969	—	pF	V_{DS} = -30V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	57	—		
Reverse Transfer Capacitance	C_{rss}	—	44	—		
Gate Resistance	R_G	—	13.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	8.2	—	nC	V_{DS} = -30V, I_D = -12A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	17.2	—		
Gate-Source Charge	Q_{gs}	—	3.0	—		
Gate-Drain Charge	Q_{gd}	—	3.1	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.4	—	ns	V_{GS} = -10V, V_{DS} = -30V, R_{GEN} = 3Ω, I_D = -12A
Turn-On Rise Time	t_R	—	23	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	34	—		
Turn-Off Fall Time	t_F	—	42	—		
Body Diode Reverse Recovery Time	t_{RR}	—	13.2	—	ns	I_S = -12A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	6.18	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

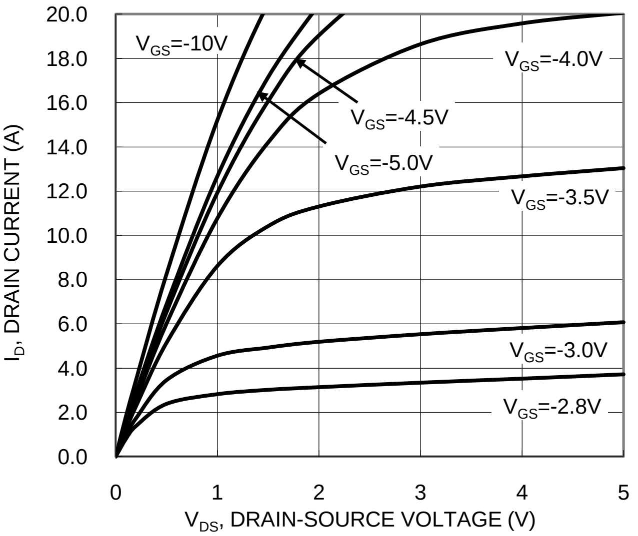


Figure 1. Typical Output Characteristic

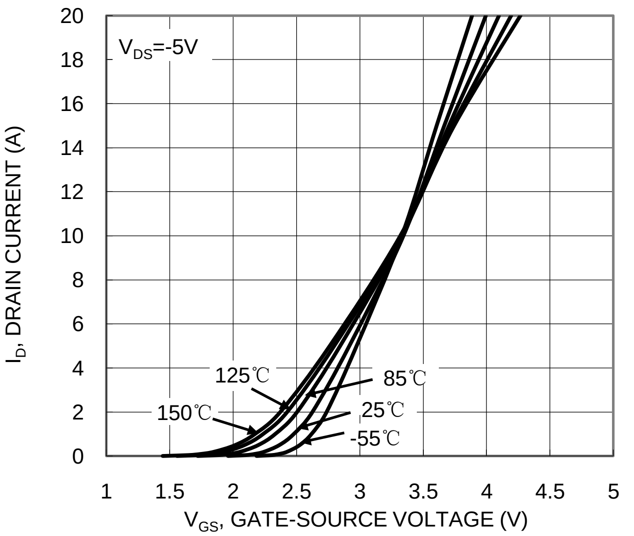


Figure 2. Typical Transfer Characteristic

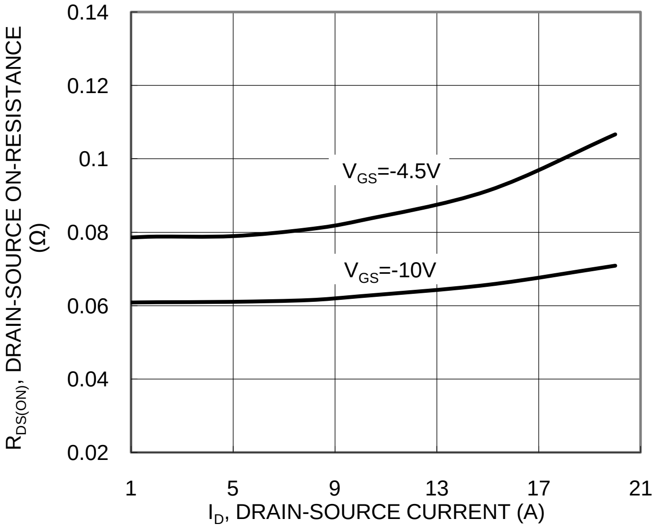


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

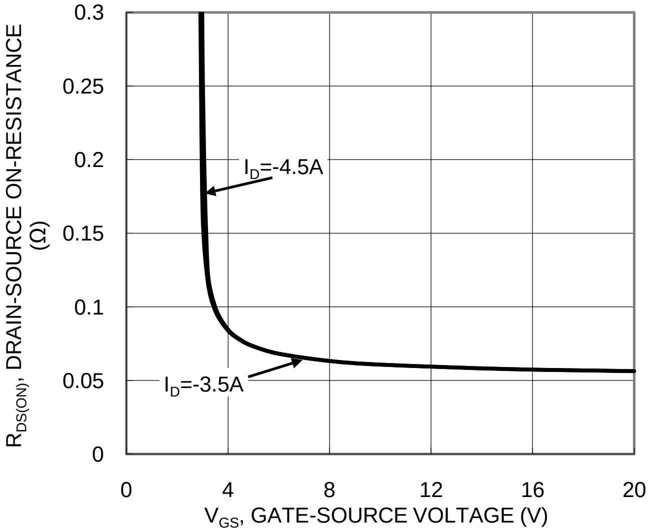


Figure 4. Typical Transfer Characteristic

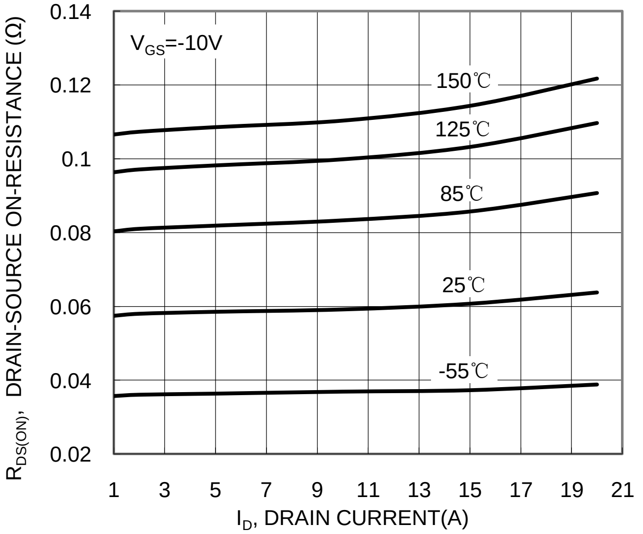


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

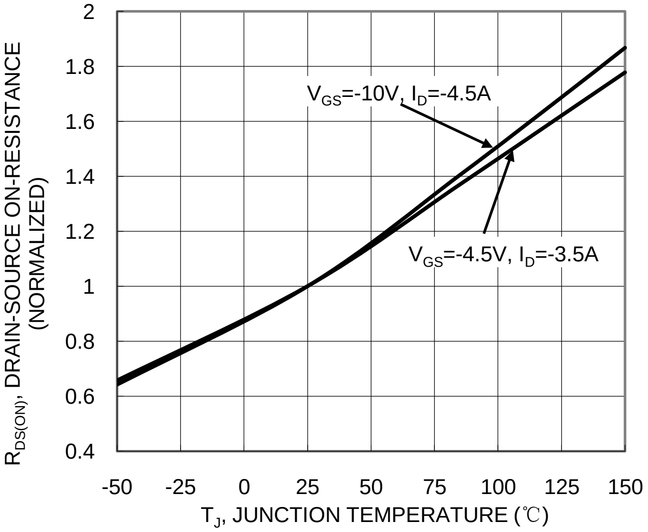


Figure 6. On-Resistance Variation with Temperature

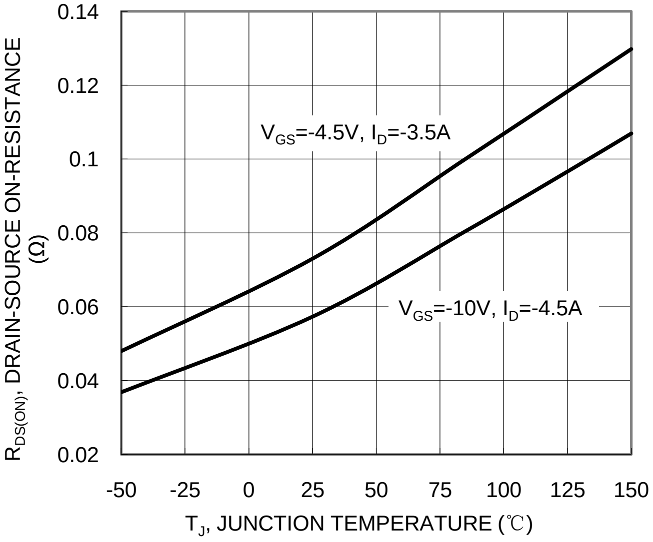


Figure 7. On-Resistance Variation with Temperature

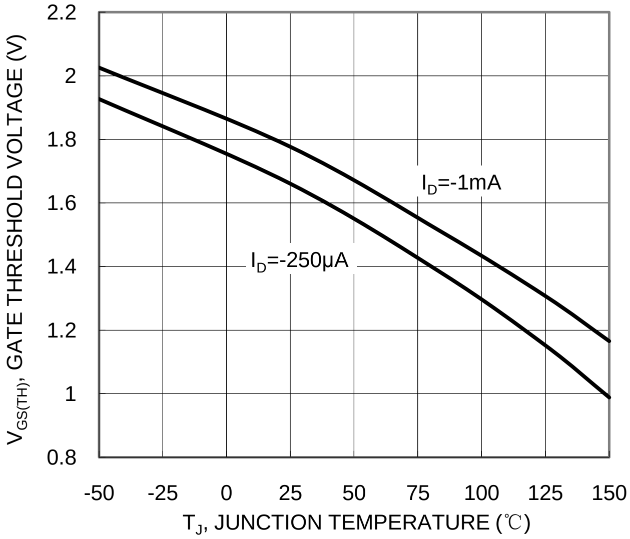


Figure 8. Gate Threshold Variation vs. Junction Temperature

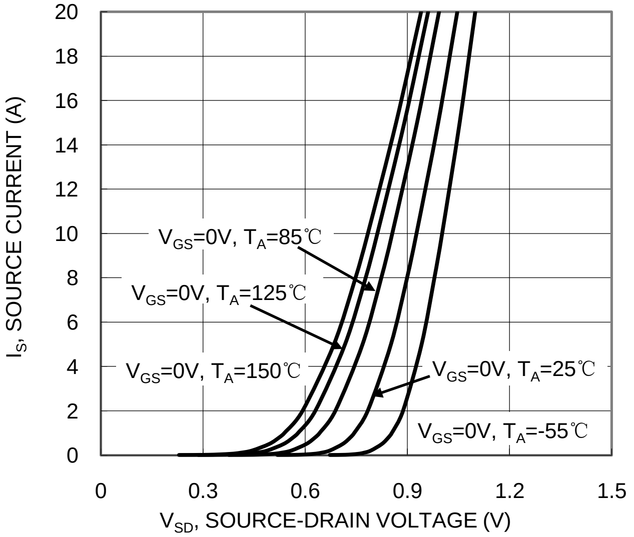


Figure 9. Diode Forward Voltage vs. Current

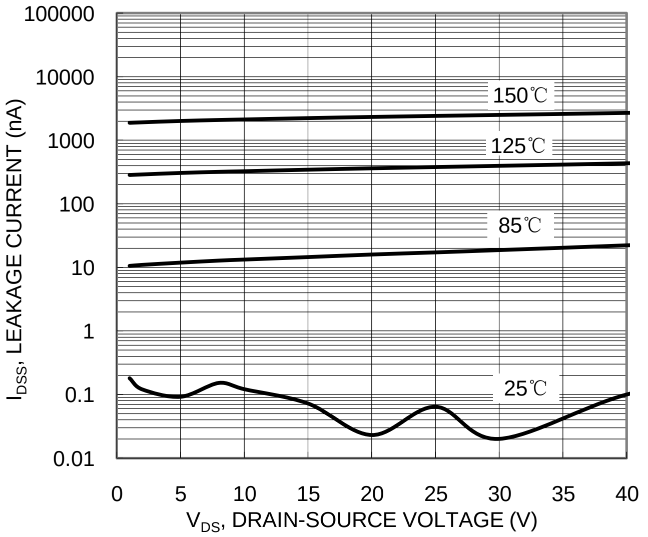


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

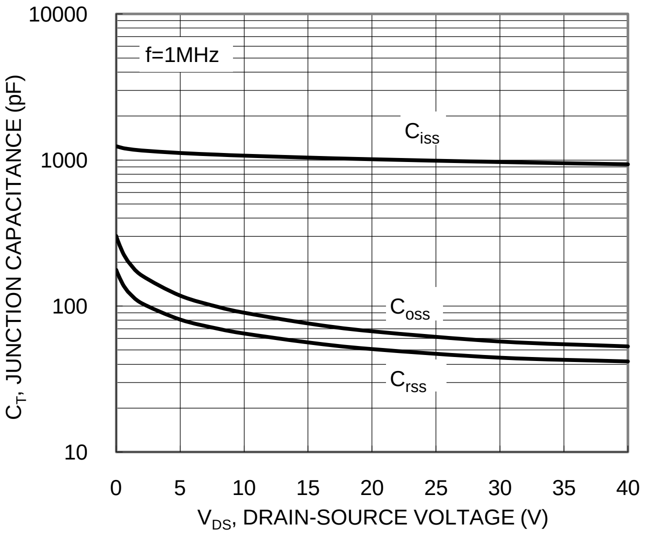


Figure 11. Typical Junction Capacitance

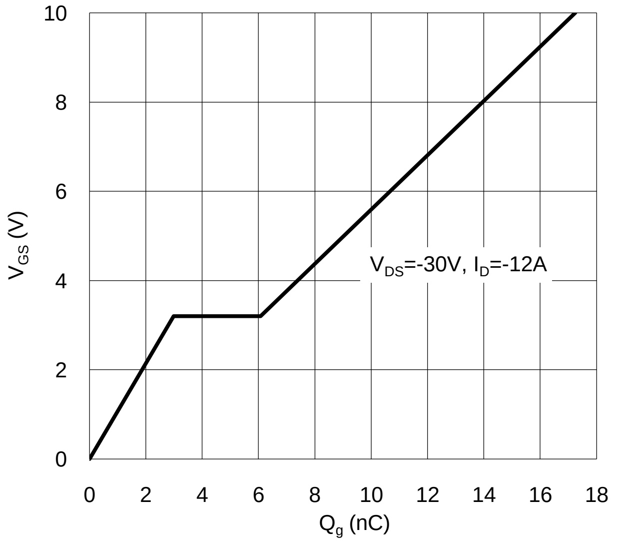


Figure 12. Gate Charge

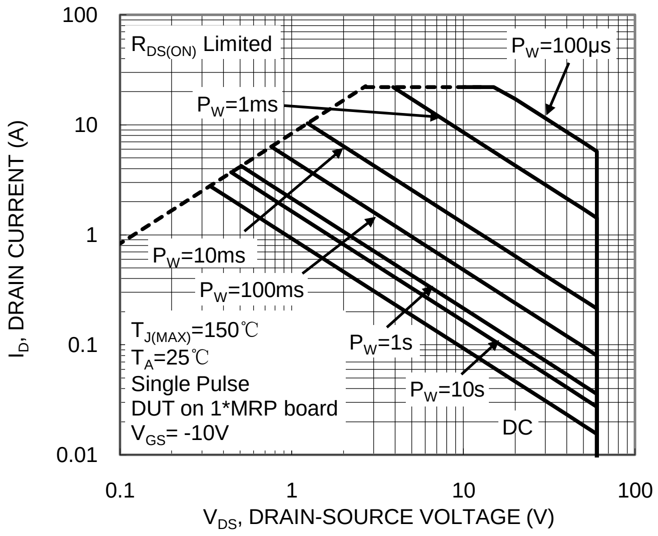


Figure 13. SOA, Safe Operation Area

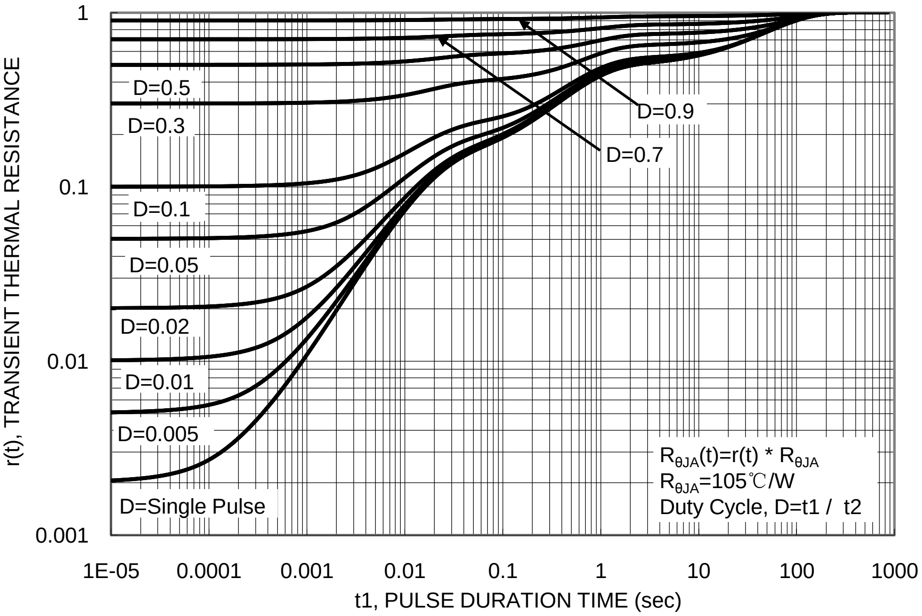
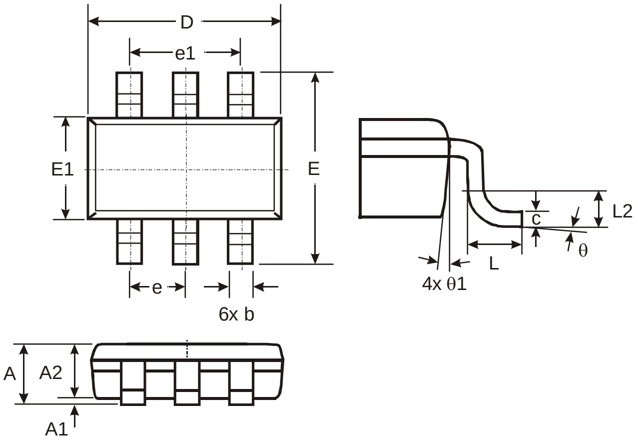


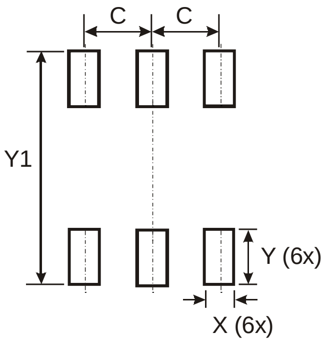
Figure 14. Transient Thermal Resistance

Package Outline Dimensions



TSOT26			
Dim	**Min**	**Max**	**Typ**
A	–	1.00	–
A1	0.01	0.10	–
A2	0.84	0.90	–
D	–	–	2.90
E	–	–	2.80
E1	–	–	1.60
b	0.30	0.45	–
c	0.12	0.20	–
e	–	–	0.95
e1	–	–	1.90
L	0.30	0.50	
L2	–	–	0.25
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199